Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
1 BRS	L1	1253	((fixed ground)adj2 (potential voltage reference)) and (soi silicon adj1 insulator)	USPAT; US-PGPUB	2002/09/12 16:58		
2 BRS	L2	2111	((source and drain)same (shall$4 deep$3 depth)) and UB	USPAT; US-PGPUB	2002/09/12 16:58		
3 BRS	L3	198	2 and (partial$3 groov$3 shallow trench$2 sti pti isolation$2)	USPAT; US-PGPUB	2002/09/12 16:59		
4 BRS	L4	62	((deplet$3) near5 (partial$2 full$3)) and 3	USPAT; US-PGPUB	2002/09/12 16:46		
5 BRS	L5	62	(@ad<=20010110 7) and 4	USPAT; US-PGPUB	2002/09/12 16:59		
6 BRS	L6	51	((fixed ground)adj2 (potential voltage reference)) and (soi silicon adj1'insulator)	EPO; JPO; DERWENT; IBM_TDB	2002/09/12 16:50		
7 BRS	L7	0	((source and drain)and (shall$4 deep$3 depth))and 6	EPO; JPO; DERWENT; IBM_TDB	2002/09/12 16:51		

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition
8 BRS	L8	11	(source and drain) and 6	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:52		
9 BRS	L9	5	6 and (partial$3 groov$3 shallow trench$2 sti pti isolation$2)	EPO; JPO; DERWEN T; IBM_TD B	2002/09/12 16:56		
10 BRS	L10	8025	(soi silicon adj1 insulator)	USPAT; US-PGP UB	2002/09/12 16:58		
11 BRS	L11	927	((source and drain) same (shall$4 deep$3 depth)) and 10	USPAT; US-PGP UB	2002/09/12 16:58		
12 BRS	L12	89	(((source and drain) with (shall$4 deep$3 depth)) same (deplet$4)) and 10	USPAT; US-PGP UB	2002/09/12 16:59		
13 BRS	L13	84	12 and (partial$3 groov$3 shallow trench$2 sti pti isolation$2)	USPAT; US-PGP UB	2002/09/12 16:59		
14 BRS	L14	84	(@ad<=20010107) and 13	USPAT; US-PGP UB	2002/09/12 17:00		
15 BRS	L15	67	14 not 5	USPAT; US-PGP UB	2002/09/12 17:00		